



<b>INFORMATION DISCLOSURE STATEMENT</b>	Atty. Docket No.: 150.01170103	Serial No.: 10/669,384
	Applicant(s): Basceri et al.	Confirmation No.: <del>Unassigned</del> 3937
	Application Filing Date: September 24, 2003	Group: <del>Unassigned</del> Art Unit 2811
	Information Disclosure Statement mailed: December <u>22</u> , 2003	

## U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
A.O.A.		5,270,241	12/14/93	Dennison et al.			
A.O.A.		5,555,486	09/10/96	Kington et al.			
A.O.A.		6,117,689	09/12/00	Summerfelt			
A.O.A.		6,333,537	12/25/01	Arita			
A.O.A.		6,337,239	01/08/02	Dehm et al.			
A.O.A.		6,372,291	04/16/02	Hua et al.			
A.O.A.		6,482,736	11/19/02	Basceri et al.			
A.O.A.		6,534,357	03/18/03	Basceri et al.			
A.O.A.		US 2003/0001190 A1	01/02/03	Basceri et al.			

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		None						

## OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copy Enclosed	Document Description
A.O.A.	X	McGuire, "Semiconductor Materials and Process Technology Handbook," Noyes Publ., Nowich, NY, 1988: 291.
A.O.A.	X	Oh et al., "Thermal Stability of RuO <sub>2</sub> /Ru Bilayer Thin Film in Oxygen Atmosphere," <i>Thin Solid Films</i> , 2000;359: 118-123.
A.O.A.		Yoon et al., "Investigation of RuO <sub>2</sub> - Incorporated PT layer as a Bottom Electrode and Diffusion Barrier for High Epsilon Capacitor Applications," <i>Electrochem. and Solid-State Lett</i> , 2000;3(8):373-376.

EXAMINER  <i>a.o.a.</i>	Date Considered  <i>21 June 2006</i>
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	